

Supplementary Materials

# TiN–Fe Vertically Aligned Nanocomposites Integrated on Silicon as A Multifunctional Platform Toward Device Applications

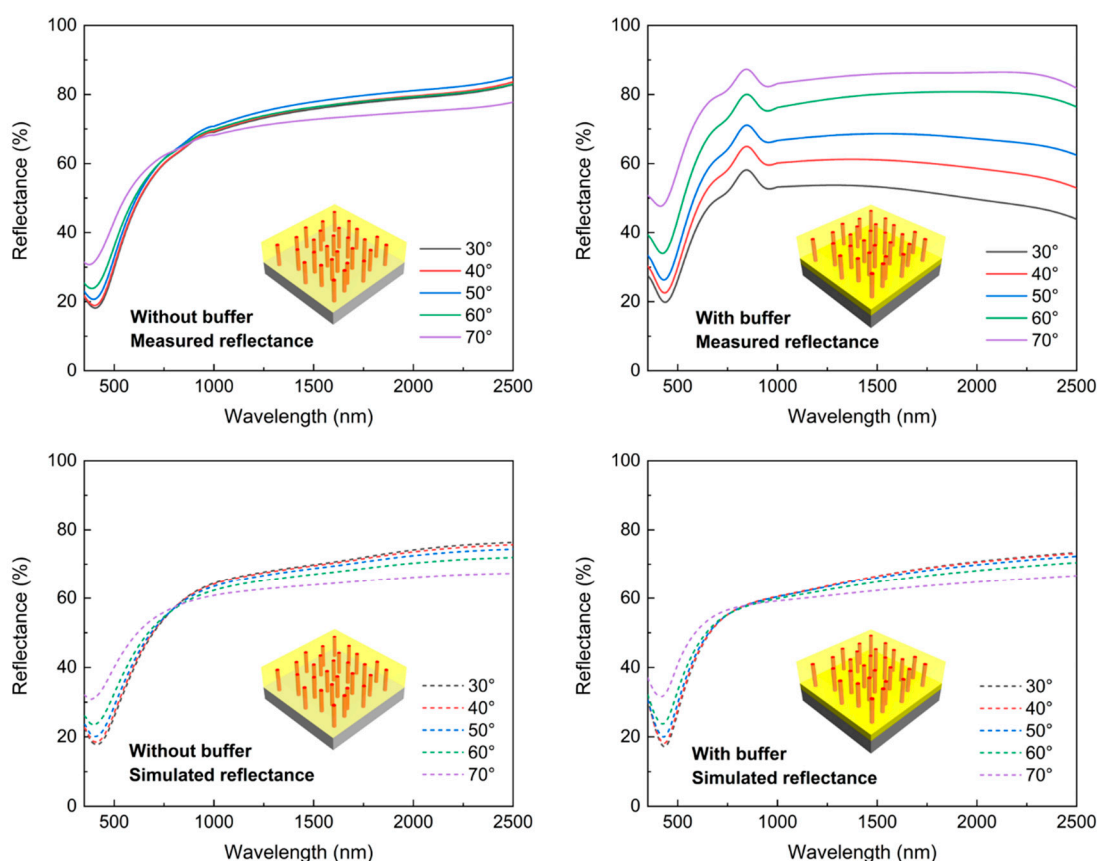
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**Figure S1.** Measured reflectance (R%) spectra of the TiN–Fe nanocomposite films deposited on Si with and without a TiN buffer layer. Simulated R% spectra of the TiN–Fe films deposited on Si with and without a TiN buffer layer.